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AIP/APL

# 1 Polarization near Dislocation Cores in SrTiO<sub>3</sub> Single Crystals: The Role of 2 Flexoelectricity

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7 Spontaneous polarization as large as  $\sim 28 \mu\text{C}/\text{cm}^2$  was recently observed around  
8 the dislocation cores in non-polar SrTiO<sub>3</sub> bulk crystals, and its origin was attributed  
9 to the flexoelectric effect, i.e., polarization induced by strain gradients. However,  
10 the roles of flexoelectricity, relative to other electromechanical contributions, and the  
11 nature of dislocations, i.e. edge versus screw dislocations in the induced polarization  
12 are not well understood. In this work, we study the role of flexoelectricity in inducing  
13 polarization around three types of dislocation cores in SrTiO<sub>3</sub>:  $b = a(100)$  edge dislo-  
14 cation,  $b = a(110)$  edge dislocation, and  $b = a(010)$  screw dislocation, where  $b$  is the  
15 Burgers vector. For the edge dislocations, polarization can be induced by electrostric-  
16 tion alone while flexoelectricity is essential for stabilizing the symmetric polarization  
17 pattern. The shear component of the flexoelectric tensor has a dominant effect on  
18 the magnitude and spatial distribution of the flexoelectric polarization. In contrast,  
19 no polarization is induced around the  $b = a(010)$  screw dislocation through either  
20 electrostriction or flexoelectricity. Our findings provide an in-depth understanding of  
21 the role of flexoelectricity in inducing polarization around dislocation cores and offer  
22 insights to the defect engineering of dielectric/ferroelectric materials.

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23  $\text{SrTiO}_3$  is a quantum paraelectric material that undergoes a transition from cubic to  
 24 tetragonal in its bulk single-crystal form upon cooling below the antiferrodistortive tran-  
 25 sition temperature of 105 K. Its transverse optical mode softens near 0 K, although no  
 26 ferroelectric transition is observed<sup>1-4</sup>. However, ample experimental evidence exists that  
 27 ferroelectricity can be induced in  $\text{SrTiO}_3$  through methods such as non-stoichiometry<sup>5,6</sup>,  
 28 strain engineering<sup>7-10</sup>, and isotope substitution<sup>11</sup>.

29 Recently, polar regions are observed around  $\text{SrTiO}_3$  dislocation cores<sup>12</sup>, and their ap-  
 30 pearance is attributed to flexoelectricity, a coupling effect between polarization and strain  
 31 gradient<sup>13-15</sup>. As a 4th rank tensor, flexoelectricity is present in crystals of all symmetries,  
 32 unlike piezoelectricity, which is absent in centrosymmetric materials. Although a universal  
 33 property, the flexoelectric coupling effect is expected to manifest itself only in materials  
 34 of large dielectric permittivity and under sufficiently large strain gradients<sup>15-20</sup>. In some  
 35 ferroelectric thin film systems<sup>21,22</sup>, researchers have observed strain gradient up to  $10^6$  /m,  
 36 which is large at long-scale but not enough to induce flexoelectric polarization. The locally  
 37 distorted regions around dislocation cores are known to possess large strain gradients, which  
 38 can reach up to approximately  $10^8$  /m as shown in our simulation, and may give rise to  
 39 flexoelectric polarization. However, it is known that other electromechanical coupling ef-  
 40 fects, such as electrostriction, can also stabilize ferroelectric phases<sup>23,24</sup>. For ferroelectric  
 41 materials, it is well-known that dislocations influence the polarization domain structure<sup>25,26</sup>.  
 42 However, it is extremely challenging, if not possible to explicitly separate the contributions  
 43 of spontaneous polarization, electrostriction, piezoelectricity, and flexoelectricity to the to-  
 44 tal polarization through experiments. Therefore, using a dielectric material like  $\text{SrTiO}_3$  as  
 45 a model system is desirable because it allows us to ignore the contribution of spontaneous  
 46 polarization and piezoelectricity since bulk  $\text{SrTiO}_3$  is not ferroelectric/piezoelectric at room  
 47 temperature. In this work, we use phase-field simulations to investigate the contributions of  
 48 flexoelectricity and electrostriction to polarization around dislocation cores in bulk single-  
 49 crystal  $\text{SrTiO}_3$ . Our phase-field ferroelectric model provides a self-consistent way to isolate  
 50 and compare the relative contributions of each flexoelectric component.

51 It is worth noting that the presence of dislocations in  $\text{SrTiO}_3$  itself may generate a  
 52 number of complex phenomena<sup>27</sup> such as the interaction of dislocation cores with oxy-  
 53 gen vacancies<sup>28-30</sup>, the stabilization of local polarization at and near dislocation cores<sup>12</sup>,  
 54 the dislocation reactions and dynamics<sup>31-33</sup>. In this work, we focus on the mechanical ef-

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55 fect arising from the presence of three common types of dislocations, the  $b = a(100)$  edge  
 56 dislocation, which is widely observed at small angle grain boundaries<sup>12,30</sup> or in plastically  
 57 deformed crystals at high temperature<sup>34–36</sup>, the  $b = a(110)$  edge dislocation, and  $b = a(010)$   
 58 screw dislocation, which are commonly observed in  $\text{SrTiO}_3$  that undergoes plastic deforma-  
 59 tion at low temperature<sup>34,35,37</sup>. The polarization and local strain distributions around the  
 60  $b = a(100)$  edge dislocation have already been characterized in the literature using high-  
 61 resolution STEM<sup>30</sup>, providing comparisons for the  $b = a(100)$  edge dislocation results of  
 62 Four phase-field calculations.

63 For all three types of dislocations, only one single dislocation is introduced in all cases.  
 64 In the real world, however,  $b = a(110)$  edge dislocation may dissociate into a pair of par-  
 65 tial dislocations, but that is beyond the discussion of this paper. We also recognize that  
 66 the dislocation core may be charged, which definitely will influence the local polarization  
 67 distribution. The effect of charges at the dislocation core on the local polarization will be  
 68 addressed in a future publication.

69 The phase-field method is employed to simulate the polarization evolution of bulk  $\text{SrTiO}_3$   
 70 in the presence of dislocations<sup>23,38</sup>. The temporal evolution of local polarization and oxygen  
 71 octahedral tilt can be described by the time-dependent Ginzburg Landau (TDGL) equation  
 72 (S1) with two sets of order parameters  $P$ , the polarization, and  $Q$ , the oxygen octahedral  
 73 tilt. Detailed forms for each free energy term are presented in Equation S3 to S7 of the  
 74 supplementary material. Comparisons between the numerical and analytical stress distri-  
 75 butions are shown in Figure S1. The strain distributions for all three types of dislocations  
 76 are shown in Figure S2.

77 A self-consistent steady-state order parameter distribution can be obtained through the  
 78 coupled solution of TDGL equation (S1), mechanical equilibrium equation (S8), and Poisson  
 79 equation (S9). All coefficients are listed in the supplementary material table (S1), which  
 80 are the same as in reference<sup>39</sup>. More details of the simulation setup and how we choose the  
 81 flexoelectric coefficients for all cases are explained in Figure S3.

82 Figure 1 shows the stress distribution and strain gradient distribution around  $b = a(100)$   
 83 edge dislocation.  $\sigma_{11}$  has the largest magnitude because it is directly affected by the disloca-  
 84 tion eigenstrain due to the additional atomic plane inside the dislocation loop. Electrostric-  
 85 tion, as a quadruple relationship between strain and polarization, can affect the shape of  
 86 total free energy in Equation S2, and thus equilibrium polarization value<sup>40</sup>. This is illustrated

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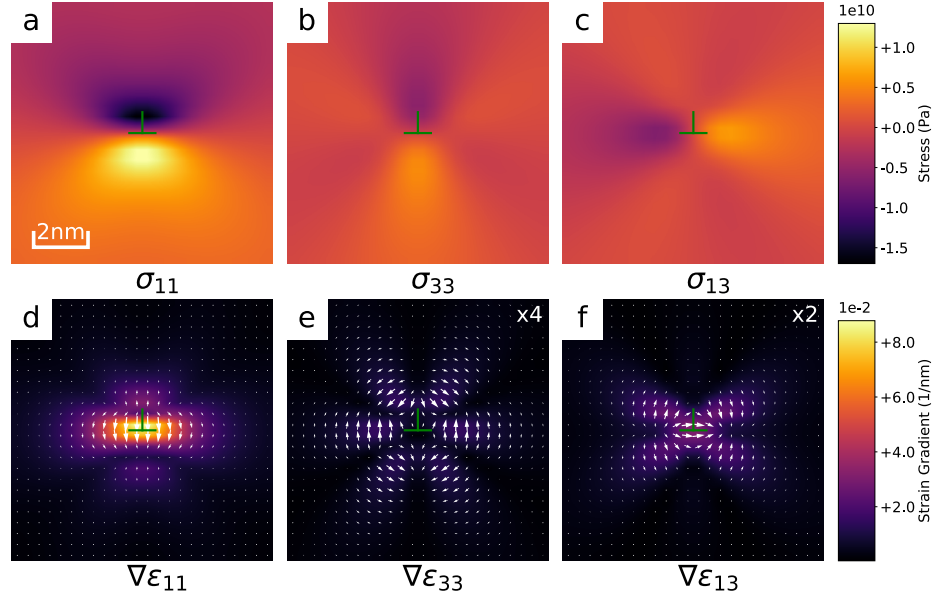


FIG. 1. Stress and strain gradient distributions around  $b = a(100)$  edge dislocation core. Background color shows the magnitude of the corresponding data, (a)  $\sigma_{11}$ , (b)  $\sigma_{33}$ , (c)  $\sigma_{13}$ , (d)  $\nabla\epsilon_{11}$ , (e)  $\nabla\epsilon_{33}$ , (f)  $\nabla\epsilon_{13}$ . Subscript 1 means the horizontal axis to the right, subscript 3 means the vertical axis to the up, and the y axis is pointing into the paper. The dislocation core is located at the center of the region marked by the green T. White arrows in (d), (e), and (f) is the gradient vector with scaling factor shown at the top right corner.

in Figure S4 that a moderate tensile stress leads to the ferroelectric phase with polarization along the tensile direction, while compressive stress still leads to the paraelectric phase. The flexoelectric effect, on the other hand, correlates the polarization orientation to the strain gradient, which breaks the central symmetry and stabilizes the ferroelectric phase directly.

The strain gradient distribution in Figure 1(d), (e), and (f), shows that the gradients of  $\epsilon_{11}$  and  $\epsilon_{33}$  are mainly along (001) direction while  $\epsilon_{13}$  gradient is along (100) direction. Additionally, the  $\epsilon_{11}$  gradient has the largest magnitude, nearly three times those of  $\epsilon_{33}$  and  $\epsilon_{13}$ . To activate the flexoelectric effect, a significant strain gradient and a large flexoelectric coefficient are two necessities. Since  $\epsilon_{11,3}$  dominates among all strain gradients in the  $b = a(100)$  edge dislocation case, according to the relationship  $E_3^{flexo} = V_{3333}\epsilon_{33,3} + V_{3311}\epsilon_{11,3} + 2V_{3113}\epsilon_{13,1}$ , the flexoelectric field along the z-direction has the largest value, thus we will

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naturally expect the polarization to be along the z-direction. Surprisingly, the simulation results prove our intuition wrong, the reason for which will become clear as we discuss the results in Figure 2 and 3.

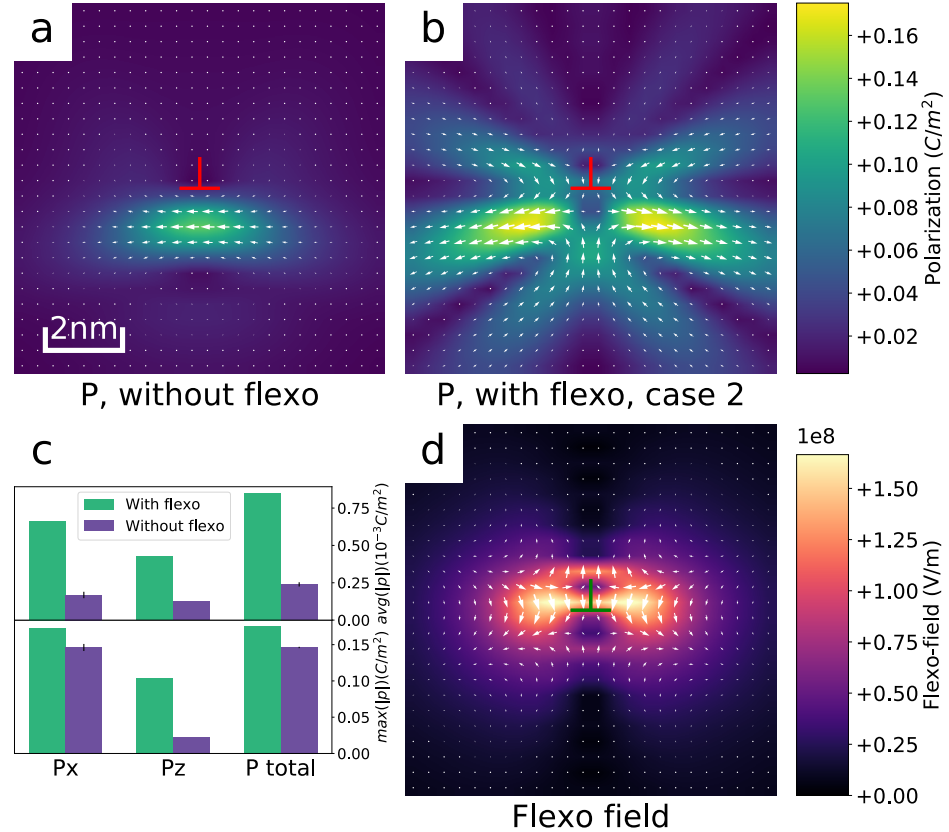


FIG. 2. Comparison of polarization distributions with and without flexoelectric effect. (a) Polarization distribution without flexoelectricity. (b) Polarization distribution considering flexoelectricity,  $V_{1111} = 0.08$  V,  $V_{1122} = 2.6$  V,  $V_{1212} = 2.2$  V. The quivers in (a),(b) indicate the polarization vector and the background heat plot illustrates the magnitude of polarization. (c) Statistics of the average and maximum Px, Pz, and P total. (d) Flexoelectric field distribution, quivers indicate the flexoelectric field and the background heat plot shows the magnitude of the flexoelectric field.

The polarization distributions with and without the flexoelectric contribution are shown in Figure 2. The result in Figure 2(a) is consistent with the analysis in Figure 1(a) and

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Figure S4(b,c) that when considering only electrostriction, it is possible to stabilize the polar state in the tensile region below the dislocation core with the polarization orienting along the tensile stress direction, while the material remains in the paraelectric phase in the compressive region above the dislocation core. The reason why the polarization in Figure 2(a) is pointing towards the left is merely due to the initial random noise. We have also observed the other degenerate state with polarization pointing towards the right if starting from a different initial noise. Figure 2(b) shows that when flexoelectricity is taken into consideration (case 2 setup), the polarization becomes mirrored with respect to the z-axis. The flexoelectric field in Figure 2(d) demonstrates more clearly the symmetric relationship of the flexoelectric driving force for polarization around the dislocation core. However, the final polarization distributions are totally different from the flexoelectric field, indicating that though there is a significant change in polarization pattern when flexoelectricity is considered, the electrostrictive effect still plays an important role in determining the final polar state in Figure 2(b). We can draw the same conclusion based on the fact that the polarization distributions in Figure 2(b) have a much larger magnitude in the tensile region below the defect compared to the compressive region above the dislocation. The bar plot in Figure 2(c) shows that flexoelectricity significantly boosts the average polarization magnitude within the plotted region because the "with flexoelectricity" case shows a much larger influential region than the "without flexoelectricity" case. On the other hand, flexoelectricity has a limited effect on the value of maximum polarization, since the maximum always appears below the dislocation in the tensile region where the role of flexoelectricity is more of reorienting the polarization that is already stabilized by electrostriction. The large increase in the maximum  $P_z$  value is because in the pure electrostriction case the tensile strain along the x-direction suppresses the occurrence of polarization along the z-axis.

To further understand the influence of flexoelectricity, we took advantage of simulation and performed a series of calculations varying the flexoelectric coefficients. Figure 3 shows the polarization and flexoelectric field distributions for three sets of flexoelectric coefficients. Comparing the polarization patterns in Figure 3 (a), (b), and (c) with the ones in Figure 2(a) and (b), we find that Figure 3(c) resembles Figure 2(b), both have the mirrored shape, while Figure 3(a) and (b) roughly maintain the uni-directional distribution as in the "without flexoelectricity" case in Figure 2(a). These results indicate that for the  $b = a(100)$  edge dislocation case,  $V_{1212}$  plays a more important role in shaping the polarization distribution

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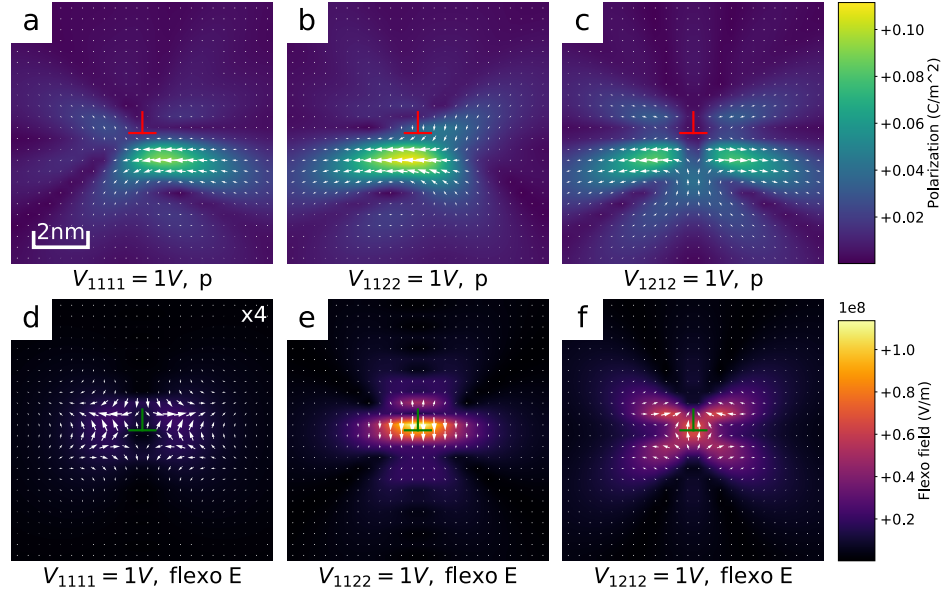


FIG. 3. The polarization and flexoelectric field distributions under different flexoelectric coefficients for  $b = a(100)$  edge dislocation. White quiver represents the plotted vector field, and the background heat plot shows the magnitude of the vector. (a, b, c) Polarization distribution. (d, e, f) Flexoelectric field distribution. (a, d) Non-zero longitudinal flexoelectric coefficient. (b, e) Non-zero transverse flexoelectric coefficient. (c, f) Non-zero shear flexoelectric coefficient.

than the other two independent flexoelectric coefficients. As shown in Figure 1 and S5, a non-zero  $V_{1111}$  activates  $\epsilon_{11,1}$  and  $\epsilon_{33,3}$ , but because both strain gradients and the coefficient are small, the magnitude of flexoelectric field in Figure 3(d) is small and thus the polarization pattern is only slightly changed compared to the "without flexoelectricity" case. Non-zero  $V_{1122}$  value leads to a huge z component in the flexoelectric field due to the large  $\epsilon_{11,3}$  value, but such a large driving force does not transform into enhanced polarization along the z-axis. Similar to how strain engineering works in epitaxial thin film, tensile strain favors polarization along the same tensile direction, but not the perpendicular direction<sup>23,40</sup>. While for  $V_{1212}$ , the combination of  $V_{1212}$  and  $\epsilon_{13,3}$  aligns the largest flexoelectric field along the x-direction, as shown in Figure S5, thus stabilizing a symmetric polarization distribution with respect to the dislocation inclusion plane along the x-direction. Some papers suggest that the flexoelectric coefficient may be negative<sup>20,41,42</sup>, so we performed several additional



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simulations with negative flexoelectric coefficients as shown in Figure S6. To make the discussion more complete, Figure S7 shows the case with zero electrostrictive coefficients while maintaining non-zero flexoelectric coefficients.

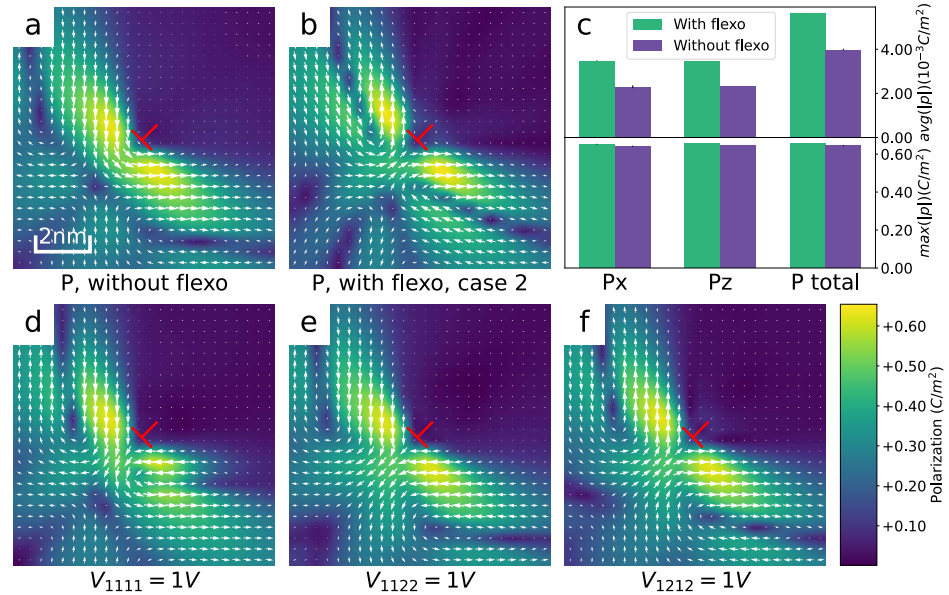


FIG. 4. The polarization distribution under different flexoelectric coefficients for  $b = a(110)$  edge dislocation. (a) No flexo. (b) Experimental flexoelectric coefficient  $V_{1111} = 0.08$  V,  $V_{1122} = 2.6$  V,  $V_{1212} = 2.2$  V. (c) Statistics of the average and maximum Px, Pz and P total. (d) Non-zero longitudinal flexoelectric coefficient. (e) Non-zero transverse flexoelectric coefficient. (f) Non-zero shear flexoelectric coefficient.

Next, we perform the same set of calculations and analysis for  $b = a(110)$  edge dislocation. In this case, the stress/strain tensor is rotated by  $45^\circ$ , and Burgers vector is longer compared to the  $b = a(100)$  edge dislocation, which leads to a larger maximum stress/strain component and a rotated strain gradient vector (see Figure S2 and S8), both have a significant influence on the polarization distribution.

As shown in Figure 4(a), a ferroelectric phase can be stabilized by  $b = a(110)$  edge dislocation through the electrostrictive effect alone. It has a much larger polarization magnitude and area compared to the  $b = a(100)$  edge dislocation case due to the larger stress/strain values around the  $b = a(110)$  edge dislocation core. When flexoelectricity is considered, as



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159 shown in Figure 4(b), the flexoelectric field reshapes the polarization into a roughly sym-  
160 metric pattern with respect to the dislocation inclusion plane. The bar plot in Figure 4(c)  
161 displays the average and the maximum polarization magnitudes within the plotted region.  
162 We observe that, firstly, both the average and maximum values are several times larger  
163 than those of the  $b = a(100)$  edge dislocation case due to a much larger local stress/strain  
164 distribution. Secondly, flexoelectricity can increase the average polarization value, while it  
165 has little effect on the maximum polarization.

166 In Figure S9 and Figure 4 (d), (e), and (f) we isolate the contribution from each of the  
167 flexoelectric coefficients. Similar to the  $b = a(100)$  edge dislocation case, the shear flexoelec-  
168 tric coefficient has the most significant influence on polarization distributions. In all cases,  
169 the polarization is stabilized and aligned predominantly along the tetragonal directions. The  
170 electrostrictive effect primarily stabilizes the polarization by shaping the free energy profile  
171 into a double well configuration, which determines the permissible polarization directions  
172 (e.g.,  $px+$  or  $px-$ , with no inherent preference) and its magnitude. Flexoelectricity's princi-  
173 pal impact resembles that of an electric field which tilts the free energy profile, forcing the  
174 polarization to align with the flexoelectric field. The results for  $b = a(010)$  screw disloca-  
175 tion show that neither electrostriction nor flexoelectricity can stabilize any polar state, more  
176 details are discussed in Figure S10.

177 In this study, we explore the role of flexoelectricity in inducing polarization around three  
178 types of dislocation cores in bulk  $SrTiO_3$ ,  $b = a(100)$  edge dislocation,  $b = a(110)$  edge dislo-  
179 cation, and  $b = a(010)$  screw dislocation. The effects of electrostriction and flexoelectricity  
180 are compared and contributions from the longitudinal, transverse, and shear flexoelectric  
181 coefficients are also discussed. Our findings reveal that for both edge dislocation cases, elec-  
182 trostriction alone is sufficient to stabilize the spontaneous polarization within the tensile  
183 region by creating the double well free energy profile. The primary role of flexoelectricity  
184 is to align the polarization with the flexoelectric field, taking into account the restrictions  
185 of the stabilized polarization directions. This leads to a symmetric polarization distribution  
186 with respect to the dislocation inclusion plane. Consequently, it is the synergistic influence  
187 of both flexoelectricity and electrostriction that determines the final polarization pattern.  
188 Polarization values as large as  $0.18 \text{ C/m}^2$  and  $0.66 \text{ C/m}^2$  are obtained for the  $b = a(100)$   
189 edge dislocation and  $b = a(110)$  edge dislocation cases respectively, when considering the  
190 flexoelectric effect. Our study identifies that the shear component of the flexoelectric tensor

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is predominantly responsible for the polarization induced around the dislocation core. Additionally, for the  $b = a(010)$  screw dislocations, neither electrostriction nor flexoelectricity can stabilize any polar phase.

The simulations in this work largely corroborate the existing experimental observations of  $b = a(100)$  edge dislocation by explicitly analyzing the contributions of flexoelectricity and electrostriction. We predict the polarization patterns around  $b = a(110)$  edge dislocation and the absence of polarization in  $b = a(010)$  screw dislocation, both of which await validation through future experimental endeavors. Several topics require further investigation. Firstly, our results for oxygen octahedral tilt are 0 at the dislocation core, which is a natural outcome based on the current Landau parameters, but this does not compare well with experimental results. Secondly, the effect of defect charges on the polarization distribution at the dislocation core demands further study. Lastly, the interaction of multiple dislocations in  $\text{SrTiO}_3$  and its impact on the domain pattern requires a comprehensive examination.

#### SUPPLEMENTARY MATERIAL

The supplementary material includes a detailed description of the phase-field model, along with additional figures to complement our discussions.

#### ACKNOWLEDGEMENTS

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Main text

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